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Miscellaneous Useful Material

Constants

$N_A = 6.022 \cdot 10^{23} \text{ mol}^{-1}$
 $\alpha \approx 1/137$
 $m_e c^2 \approx 511 \text{ keV}$
 $m_p c^2 \approx 938 \text{ keV}$
 $m_n c^2 \approx 940 \text{ MeV}$
 $m_\pi \approx 140 \text{ MeV}$
 $m_K \approx 500 \text{ MeV}$
 $K_{BB} \approx 0.3 \text{ MeV g}^{-1} \text{ cm}^2$
 $(\beta\gamma)_{\text{MIP}} \approx 3.5, \quad \beta_{\text{MIP}} \approx 0.96$
 $1 \text{ torr} = 1 \text{ mmHg} \approx 133 \text{ Pa}$
 $k_B T|_{T=300 \text{ K}} \approx 0.025 \text{ eV}$

Some Relationships from Special Relativity

$\beta \equiv v/c \quad \gamma \equiv 1/\sqrt{1-\beta^2}$
 $E^2 = m^2 c^4 + p^2 c^2 \quad E = \gamma m c^2 \quad E = T + m c^2$
 $\gamma\beta = \frac{pc}{mc^2} \quad \gamma^2 = 1 + (\beta\gamma)^2 \quad \beta^2 = 1 - 1/\gamma^2$
 $\beta^2 = \frac{p^2 c^2}{m^2 c^4 + p^2 c^2}$
 $mc^2 = \frac{p^2 c^2 - T^2}{2T}$

Some Relationships from Chemistry

The number density n_a (n_e) of atoms (electrons) in material with density ρ , molar mass M_m and atomic number Z is...

$n_a = \frac{\rho N_A}{M_m}$ and $n_e = Z n_a$
Molar mass M_m and relative atomic mass A_r are related by...
 $M_m = A_r M_u$, where $M_u \equiv 1 \text{ g mol}^{-1}$
 $n_a \approx \frac{\rho N_A}{A M_u}$ (if $A_r \approx A$)

Ideal Gas

$V_m \approx 22.4 \text{ L mol}^{-1}$ (molar volume of ideal gas at STP)
 $p_0 = 1 \text{ atm} \approx 101 \text{ kPa}$ (atmospheric pressure)
 $n = \frac{N_A p}{V_m p_0}$ (number density of ideal gas molecules)

Statistics

Binomial distribution: the probability of n events occurring over the course of N trials, where the probability of an event occurring in a single trial is p , is given by

$$P(n|N, p) = \binom{N}{n} p^n (1-p)^{N-n} = \frac{N!}{n!(N-n)!} p^n (1-p)^{N-n}$$

Poisson distribution: the probability of n independent random events occurring in the time interval T , where the probability for an event per unit time is λ , is

$$P(n|\lambda, T) = \frac{(\lambda T)^n}{n!} e^{-\lambda T}, \text{ or...}$$

$$P(n|\mu) = \frac{\mu^n e^{-\mu}}{n!}, \quad \text{where } \mu \equiv \lambda T$$

$$\langle X \rangle = \sigma_X^2 = \lambda \quad (\text{if } X \text{ is Poisson distributed with mean } \mu)$$

Error function and standard normal distribution CDF

$$\Phi(x) = \frac{1}{2} \left[1 + \operatorname{erf} \left(\frac{x}{\sqrt{2}} \right) \right]$$

Statistical significance in signal/background classification

$n = \frac{N_{\text{sig}}}{\sigma_{\text{bg}}}$
 N_{sig} is number of counted signal events
 σ_{b} is fluctuation in background events
 $\bar{N}_{\text{sig}} = st \quad \bar{N}_{\text{bg}} = bt$ (if rates s, b are known)

Ionization-Based Detectors	
Measuring Momentum	
Semiconducting Detectors	
Scintillating Detectors	
Neutron Detection	
Cherenkov Radiation	

Interaction of Particles and Matter

Scattering Cross Section

Beam with flux F of incident particles on target; $\frac{dN_s}{d\Omega}$ is number of particles scattered into solid angle $d\Omega$ per unit time.

$$\frac{d\sigma}{d\Omega} = \frac{1}{F} \frac{dN_s}{d\Omega} \quad \sigma_{\text{tot}}(E) = \iint_{\Omega} \frac{d\sigma}{d\Omega} d\Omega$$
$$N_s(\Omega) = F S n_t \frac{d\sigma}{d\Omega} \delta x \quad N_s = F S n_t \sigma_{\text{tot}} \delta x$$

$dP_{\text{scat}} = n_t \sigma_{\text{tot}} dx$ (probability for scattering in region dx)
 $P(x+dx) = P(x) \cdot (1 - dP_{\text{scat}}) = P(x)(1 - n_t \sigma_{\text{tot}} dx)$
 $P(x) = e^{-n_t \sigma_{\text{tot}} x}$ (probability for not scattering up to x)
 $1 \text{ b} = 10^{-24} \text{ cm}^2 = 10^{-28} \text{ m}^2$

Charged Particles in Matter

Charged ionizing particle (IP) of mass m and valence Z_p travels through material with atomic number Z_m and density ρ . Assume IP is heavy ($m \gg m_e$)

Energy loss occurs primarily because of inelastic collisions of IP with electrons in the material.

Bethe-Bloch Formula

Valid for $\beta\gamma \sim (0.5, 10^3)$

$$-\frac{dE}{dx} = \frac{4\pi}{m_e c^2} \cdot \frac{n_e Z_p^2}{\beta^2} \cdot \left(\frac{e_0^2}{4\pi\epsilon_0} \right)^2 \ln \left[\left(\frac{2m_e c^2 \gamma^2 \beta^2}{Z_m I_0} \right) - \beta^2 \right]$$
$$= K \cdot \frac{\rho Z_m}{A} \cdot \frac{Z_p^2}{\beta^2} \left[\ln \left(\frac{2m_e c^2 \beta^2 \gamma^2}{Z_m I_0} \right) - \beta^2 \right]$$

$$K \approx 0.3 \text{ MeV g}^{-1} \text{ cm}^2 \quad I_0 \sim 10 \text{ eV}$$

Small β approximation (e.g. for $\beta\gamma \lesssim 1$) produces...

$$-\frac{dE}{dx} \sim \beta^{-2} \sim T^{-1} \implies \frac{dT}{dx} = -\frac{k}{T}, \quad k = -T_0 \left. \frac{dT}{dx} \right|_{T=T_0}$$

In Polyatomic Substances

Example: for H_2O_4 , $i \in \{\text{H}, \text{O}\}$, e.g. $a_{\text{H}} = 2$, $a_{\text{O}} = 4$

$$Z \rightarrow Z_{\text{eff}} = \sum_i a_i Z_i$$

$$A \rightarrow A_{\text{eff}} = \sum_i a_i A_i$$

$$\ln I \rightarrow \ln I_{\text{eff}} = \sum_i \frac{a_i Z_i \ln I_i}{Z_{\text{eff}}}$$

$$\left(-\frac{dE}{dx} \right)_{\text{tot}} = \sum_i w_i \left. \frac{dE}{dx} \right|_i, \quad w_i = \frac{a_i A_i}{\sum_j a_j A_j}$$

$$\left(-\frac{dE}{dx} \right)_{\text{tot}} = K \cdot \frac{\rho_{\text{tot}} Z_{\text{eff}}}{A_{\text{eff}}} \cdot \frac{Z_p^2}{\beta^2} \left[\ln \left(\frac{2m_e c^2 \beta^2 \gamma^2}{I_{\text{eff}}} \right) - \beta^2 \right]$$

Photons in Matter

Three processes: photoelectric effect, Compton scattering, and pair production

$$\sigma_\gamma = \sigma_{\text{pe}} + Z \cdot \sigma_{\text{C}} + \sigma_{\text{pair}}$$

$$\sigma_{\text{pe}} \sim \frac{Z^n}{E_\gamma^{n/2}}, \quad n \lesssim [4, 5]$$

$$j(x) = j_0 e^{-\mu x} \quad \mu_\gamma = n_a \sigma_\gamma = \frac{\rho N_A}{M_m} \sigma_\gamma \quad \lambda_\gamma = 1/\mu_\gamma$$

$$\mu_{\text{tot}} = \sum_i w_i \mu_i = \sum_i \left(\frac{A_i}{\sum_j A_j} \right) \mu_i \quad (\text{polyatomic substances})$$

Compton Scattering

Incident and scattered γ energies: E_γ, E'_γ ; θ scattering angle

$$\frac{E'_\gamma}{E_\gamma} = \frac{1}{1 + \alpha(1 - \cos \theta)}, \quad \alpha \equiv \frac{E_\gamma}{m_e c^2}$$

$$\frac{d\sigma}{d\Omega} = \frac{r_e^2}{2} \left(\frac{E'_\gamma}{E_\gamma} \right)^2 \left[\frac{E'_\gamma}{E_\gamma} + \frac{E_\gamma}{E'_\gamma} - \sin^2 \theta \right]$$

$$\sigma_C = \frac{8\pi r_e^2}{3} \left[\frac{1-2\alpha+1.2\alpha^2}{(1+2\alpha)^2} \right], \quad r_e = \frac{1}{4\pi\epsilon_0} \frac{e_0}{m_e c^2} \sim 2.8 \text{ fm}$$

$$\frac{d\sigma_C}{dT} = \frac{\pi r_0^2}{m_e c^2 \alpha^2} \left[2 + \frac{s^2}{\alpha^2(1-s)^2} + \frac{s}{1-s} \left(s - \frac{2}{\alpha} \right) \right], \quad s = T/E_\gamma$$

Particle Detectors

Energy Resolution

For a particle depositing energy E_{dep} and producing N ion pairs in a detector with Fano factor F ...

$$\mathcal{R} \equiv \frac{\sigma_{E_{\text{dep}}}}{E_{\text{dep}}} = \frac{\sigma_N}{N}$$

Particle passes through detector: $\sigma_N = \sqrt{N}$

Particle stops inside detector: $\sigma_N = \sqrt{FN}$

$$N = \frac{E_{\text{dep}}}{w_i} \implies \mathcal{R} = \sqrt{\frac{w_i}{E_{\text{dep}}}} \quad \text{or} \quad \mathcal{R} = \sqrt{\frac{F w_i}{E_{\text{dep}}}}$$

Ionization-Based Detectors

Parallel-Plate Ionization Cell

Consider a parallel-plate cell with pressure p , spacing d , potential difference U and constant electric field $E = U/d$.

$$dW = qE dx = \frac{qU}{d} dx \quad (\text{work on a charge } q)$$

$$dW_C = CU dU \quad (\text{change in capacitor energy})$$

$$dW = dW_C \implies dU = \frac{q}{C} \frac{dx}{d}$$

$$v_d = \frac{E\mu}{p} \quad (\text{drift velocity, mobility})$$

$$\Delta U(t) = \frac{q}{pd} Et \quad (\text{before all ions reach electrodes})$$

$$\Delta U = \frac{Q}{C} \quad (\text{when total charge } Q \text{ reaches electrodes})$$

Multiplication Factor

For an incident particle freeing N_0 primary ions, which in turn free an average of N secondary ions...

$$M \equiv \frac{N}{N_0} \quad (\text{multiplication factor})$$

λ is electron mean free path for ionizing collisions

$\alpha \equiv 1/\lambda$ is probability for ionization per distance traveled

$$dN = N\alpha dx \implies N(x) = N_0 e^{\alpha x} \quad (\text{for } N \text{ initial electrons})$$

$$M(x) \equiv N/N_0 = e^{\alpha x} \quad \text{or} \quad M = \exp \left(\int_{x_1}^{x_2} \alpha(x) dx \right)$$

In a cell at pressure p with electric field E ...

$$\alpha = Ape^{-\frac{Bp}{E}} \quad (\text{Townsend discharge model; } A, B \text{ given})$$

Cylindrical Ionization Chamber

For a cylindrical chamber with outer radius R and anode wire radius r_0 at voltage U_0 ...

$$E(r) = \frac{U_0}{\ln(R/r_0)} \frac{1}{r} \quad \phi(r) = -\frac{U_0}{\ln(R/r_0)} \ln \frac{r}{r_0} \quad C = \frac{2\pi\epsilon_0 L}{\ln(R/r_0)}$$

$$v_d = E\mu \quad (\text{drift velocity } v_d, \text{ mobility } \mu)$$

Signal detection delay t_{sig} between ionization event at $r = r^*$ and primary electrons reaching anode wire is...

$$t_{\text{sig}} = \frac{\ln(R/r_0)R^2}{2\mu_e U_0} \left[\left(\frac{r^*}{R} \right)^2 - \left(\frac{r_0}{R} \right)^2 \right] \approx \frac{\ln(R/r_0)}{2\mu_e U_0} (r^*)^2$$

Only secondary positive ions contribute appreciably to signal

$$U(t) = -\frac{Q_i}{4\pi\epsilon_0 L} \ln \left[1 + \frac{\mu_i C U_0}{\pi\epsilon_0 L r_0^2} \cdot (t - t_{\text{sig}}) \right] \equiv -\frac{Q_i}{4\pi\epsilon_0 L} \ln \left(1 + \frac{t - t_{\text{sig}}}{t_0} \right)$$

$$U(t) = -\frac{N_s e_0}{4\pi\epsilon_0 L} \begin{cases} \approx 0 & t < t_{\text{sig}} \\ \ln \left(1 + \frac{t - t_{\text{sig}}}{t_0} \right) & t_{\text{sig}} < t < t_{\text{sig}} + t_{\text{ion}} \end{cases}$$

$$t_0 \equiv \frac{\pi\epsilon_0 L r_0^2}{\mu_i C U_0}, \quad t_{\text{ion}} \approx \frac{\ln(R/r_0)}{2\mu_i U_0} R^2$$

$$N_s = M N_p = M \frac{E_{\text{dep}}}{w_i}$$

Measuring Momentum

Use a central drift chamber with beamline axis \hat{z} and magnetic field $\mathbf{B} \approx B\hat{z}$

For particle of charge q with trajectory curvature radius R ...

$$\frac{mv_{\perp}^2}{R} = qv_{\perp} B \implies p_{\perp} = qBR \quad (\text{very simplified})$$

$$p_{\text{TC}} \approx (0.3qBR) \text{ GeV} \dots$$

... if q is measured in e_0 , B in tesla and R in meters

Momentum resolution $\sigma_{p_{\perp}}$ if trajectory resolution is σ_x ...

$$\frac{\sigma_{p_{\perp}}}{p_{\perp}} \approx \frac{\sqrt{96}\sigma_x}{qBL^2} \cdot p_{\perp} \quad (\text{three points on trajectory})$$

$$\frac{\sigma_{p_{\perp}}}{p_{\perp}} \approx \frac{\sigma_x}{qBL^2} \cdot \sqrt{\frac{720}{N+4}} \cdot p_{\perp} \quad (N \text{ points on trajectory})$$

L is characteristic length of cylindrical drift chamber

Semiconducting Detectors

E_v is top of valence band

E_c is bottom of conduction band

$E_g \equiv E_c - E_v$ is band gap

$$f(E) = \frac{1}{e^{\beta(E-\mu)} + 1} \quad (\text{Fermi-Dirac distribution})$$

$$g_c(E) \approx \frac{1}{2\pi^2} \left(\frac{2m_c^*}{\hbar^2} \right)^{3/2} \sqrt{|E - E_c|}$$

$$g_v(E) \approx \frac{1}{2\pi^2} \left(\frac{2m_v^*}{\hbar^2} \right)^{3/2} \sqrt{|E - E_v|}$$

$$n_c = \frac{1}{4} \left(\frac{2m_c^* k_B T}{\pi \hbar^2} \right)^{3/2} e^{-\beta(E_c - \mu)} \equiv N_c(T) e^{-\beta(E_c - \mu)}$$

$$p_v = \frac{1}{4} \left(\frac{2m_v^* k_B T}{\pi \hbar^2} \right)^{3/2} e^{-\beta(\mu - E_v)} \equiv P_v(T) e^{-\beta(\mu - E_v)}$$

$$\text{In intrinsic SC: } n_c = p_v \equiv n_i \implies n_i^2 = N_c P_v e^{-\beta E_g}$$

$$n_i = \frac{1}{4} \left(\frac{2k_B T \sqrt{m_e^* m_h^*}}{\pi \hbar^2} \right)^{3/2} e^{-\frac{\beta E_g}{2}}$$

Resistivity, Conductivity, Current Density

Consider conductor of conductivity σ_E with number density n of charge carriers q and mobility μ moving at drift velocity v_d under external electric field E

$$j = \sigma_E E \quad \text{and} \quad j = nqv_d$$

$$v_d = \mu E$$

$$\rho_E \equiv \frac{1}{\sigma_E}; \quad \rho_E = \frac{1}{nq\mu} \quad \sigma_E = nq\mu$$

$$j = e_0 n_i (\mu_e + \mu_h) E \quad (\text{in intrinsic SC})$$

$$j_n \approx e_0 N_d \mu_e E, \quad j_p \approx e_0 N_a \mu_h E \quad (\text{in doped SC})$$

$$\sigma_n \approx e_0 N_d \mu_e, \quad \sigma_p \approx e_0 N_a \mu_h \quad (\text{in doped SC})$$

p-n Junction

Join p- and n-type SCs with dopant densities N_a and N_d

Depletion region spans $x \in (-x_p, x_n)$

$$N_a x_p = N_d x_n \quad (\text{conservation of charge})$$

$$\frac{\partial^2 \phi}{\partial x^2} = -\frac{\rho(x)}{\epsilon\epsilon_0} \quad (\text{Poisson equation for potential})$$

$$\rho(x) \approx \begin{cases} -e_0 N_a & x \in (-x_p, 0) \\ e_0 N_d & x \in (0, x_n) \end{cases}$$

$$\frac{d\phi}{dx} \approx \begin{cases} \frac{e_0 N_a}{\epsilon\epsilon_0} (x + x_p) & x \in (-x_p, 0) \\ -\frac{e_0 N_d}{\epsilon\epsilon_0} (x - x_n) & x \in (0, x_n) \end{cases}$$

$$\phi(-x_p) \equiv 0 \text{ V}, \quad V_0 \equiv \phi(x_n) - \phi(-x_p) = \phi(x_n)$$

$$V_0 = \frac{e_0}{2\epsilon\epsilon_0} (N_d x_n^2 + N_a x_p^2)$$

$$\phi(x) = \begin{cases} \frac{e_0 N_a}{2\epsilon\epsilon_0} (x + x_p)^2 & x \in (-x_p, 0) \\ V_0 - \frac{e_0 N_d}{2\epsilon\epsilon_0} (x - x_n)^2 & x \in (0, x_n) \end{cases}$$

$$x_n^2 = \frac{2\epsilon\epsilon_0 V_0}{e_0 N_d (1 + \frac{N_d}{N_a})}, \quad x_p^2 = \frac{2\epsilon\epsilon_0 V_0}{e_0 N_d (1 + \frac{N_a}{N_d})}$$

$$d_{\text{pn}} = x_n + x_p = \sqrt{\frac{2\epsilon\epsilon_0 V_0}{e_0} \frac{N_a + N_d}{N_a N_d}}$$

$$d_{\text{pn}} \approx x_n \approx \sqrt{\frac{2\epsilon\epsilon_0 V_0}{e_0 N_d}} \quad (\text{if } N_a \gg N_d)$$

$$d_{\text{pn}} \approx x_p \approx \sqrt{\frac{2\epsilon\epsilon_0 V_0}{e_0 N_a}} \quad (\text{if } N_d \gg N_a)$$

$$d_{\text{pn}}^{(b)} = d_{\text{pn}}^{(0)} \sqrt{1 + \frac{V_b}{V_0}} \quad (\text{with reverse bias voltage } V_b)$$

Approximate Expressions Depletion Region Width

$$\sigma_n \approx e_0 N_d \mu_e, \quad \sigma_p \approx e_0 N_a \mu_h \implies \rho_n \approx \frac{1}{e_0 N_d \mu_e}, \quad \rho_p \approx \frac{1}{e_0 N_a \mu_h}$$

$$d_{\text{pn}} \approx \sqrt{2\epsilon\epsilon_0 \rho_n \mu_e V_0} \quad (\text{if } N_a \gg N_d)$$

$$d_{\text{pn}} \approx \sqrt{2\epsilon\epsilon_0 \rho_p \mu_h V_0} \quad (\text{if } N_d \gg N_a)$$

Using $\epsilon_{\text{Si}} \approx 12$ and $\epsilon_{\text{Ge}} \approx 16$ we get...

$$d_{\text{Si}} \approx 0.53 \sqrt{\rho_n V_0} \cdot \mu\text{m} \quad (\text{if } N_a \gg N_d)$$

$$d_{\text{Si}} \approx 0.32 \sqrt{\rho_p V_0} \cdot \mu\text{m} \quad (\text{if } N_d \gg N_a)$$

$$d_{\text{Ge}} \approx 1.00\sqrt{\rho_n V_0} \cdot \mu\text{m} \quad (\text{if } N_a \gg N_d)$$

$$d_{\text{Ge}} \approx 0.65\sqrt{\rho_p V_0} \cdot \mu\text{m} \quad (\text{if } N_d \gg N_a)$$

... assuming V_0 in volts and ρ in $\Omega\text{ cm}$

Signal Dynamics in a p-n Semiconducting Detector

Shift coordinate system so that $x_p \equiv 0$

Let x_0 denote initial position of electron-hole pair

$$\tau_h \equiv \frac{\epsilon\epsilon_0}{e_0\mu_h N_a}, \quad \tau_e \equiv \frac{\mu_h}{\mu_e} \tau_h, \quad t_e = \tau_h \frac{\mu_h}{\mu_e} \cdot \ln \frac{d_{\text{pn}}}{x_0}$$

$$Q_e(t) = +\frac{e_0}{d_{\text{pn}}} x_0 \left(1 - e^{\frac{\mu_e}{\mu_h} \frac{t}{\tau_h}}\right) \quad (\text{for } t < t_e)$$

$$Q_h(t) = -\frac{e_0}{d_{\text{pn}}} x_0 \left(1 - e^{-t/\tau_h}\right)$$

$$I_e(t) = \frac{dQ_e}{dt} = -\frac{e_0}{d_{\text{pn}}} \frac{x_0}{\tau_h} \frac{\mu_e}{\mu_h} e^{\frac{\mu_e}{\mu_h} \frac{t}{\tau_h}} \quad (\text{for } t < t_e)$$

$$I_h(t) = \frac{dQ_h}{dt} = \frac{e_0}{d_{\text{pn}}} \frac{x_0}{\tau_h} e^{-t/\tau_h}$$

$$I_0^h \equiv \frac{e_0}{d_{\text{pn}}} \frac{x_0}{\tau_h}, \quad I_0^e \equiv -\frac{e_0}{d_{\text{pn}}} \frac{x_0}{\tau_e}$$

$$U_e(t) = \frac{I_0^e R}{1+(RC)/\tau_e} \begin{cases} e^{t/\tau_e} - e^{-\frac{t}{RC}} & t < t_e \\ \left(e^{t_e/\tau_e} - e^{-\frac{t_e}{RC}}\right) e^{-\frac{(t-t_e)}{RC}} & t > t_e. \end{cases}$$

$$U_h(t) = \frac{I_0^h R}{1-(RC)/\tau_h} \left(e^{-t/\tau_h} - e^{-\frac{t}{RC}}\right),$$

Limit Cases of Electron Signal

$$U_e(t) \approx I_0^e R \begin{cases} e^{t/\tau_e} - e^{-\frac{t}{RC}} & t < t_e \\ \left(e^{t_e/\tau_e} - e^{-\frac{t_e}{RC}}\right) e^{-\frac{(t-t_e)}{RC}} & t > t_e \end{cases} \quad (RC \ll \tau_e)$$

$$U_e(t) = \frac{I_0^e \tau_e}{C} \left(e^{t_e/\tau_e} - 1\right) e^{-\frac{(t-t_e)}{RC}} = \frac{Q_e(t_e)}{C} e^{-\frac{(t-t_e)}{RC}} \quad (RC \gg \tau_e)$$

Position Measurement

Consider parallel silicon microstrips separated by *pitch* p

$$\sigma_x = \frac{p}{\sqrt{12}} \quad (\text{when using one strip to measure position})$$

$$\bar{x} = \frac{\sum_i Q_i x_i}{\sum_i Q_i} \quad (\text{using multiple strips to measure position})$$

$$\sigma_{\bar{x}}^2 \propto p^2 \frac{\sum_j \sigma_{Q_j}^2}{(\sum_i Q_i)^2} = p^2 \frac{(\text{noise})^2}{(\text{signal})^2} = \frac{p^2}{\text{SNR}^2}$$

Q_j is charge on j -th strip

$\sigma_{Q_j}^2$ is resolution of charge on j -th strip

Scintillating Detectors

Consider scintillator with time constant τ , emitting $Y \equiv \frac{dN}{dE}$ photons per unit absorbed energy and photodetector with efficiency η and multiplication factor M

$$\eta \equiv E_{\text{scint}}/E_{\text{dep}}, \quad E_{\text{scint}} = N_{\text{scint}} h\nu = hc/\lambda \quad (\text{efficiency})$$

$$N(t) = N_0 e^{-t/\tau} \quad (\text{number of scintillation photons})$$

We assume a fast photodetector, so $I(t)$ follows $N(t)$, i.e.

$$I(t) = I_0 e^{-t/\tau} \quad (\text{photodetector current})$$

$$Q = \eta e_0 M Y E_{\text{dep}} \quad (\text{photodetector charge})$$

$$Q = \int_0^\infty (t) dt = I_0 \tau \implies I_0 \tau = \eta e_0 M Y E_{\text{dep}}$$

$$U(t) = \frac{I_0 R}{1-(RC)/\tau} \left(e^{-t/\tau} - e^{-\frac{t}{RC}}\right)$$

$$U(t) \approx \frac{I_0 \tau}{C} e^{-t/\tau} = \frac{Q}{C} e^{-t/(RC)} \quad (RC \gg \tau)$$

$$U(t) \approx R I_0 e^{-t/\tau} = R I(t) \quad (RC \ll \tau)$$

Fluctuations in Photomultipliers

X is the number of secondary electrons reaching PMT anode as a result of one initial cathode photoelectron

n is the number of initial cathode photoelectrons

S is the sum of all secondary electrons reaching PMT anode

n is Poisson-distributed with mean λ

$$\langle S \rangle = \lambda \langle X \rangle$$

$$\sigma_S^2 = \lambda \langle X^2 \rangle \left(1 + \frac{\sigma_X^2}{\langle X \rangle^2}\right) \equiv F \lambda \langle X^2 \rangle$$

Neutron Detection

In a material with scattering center density n_s and neutron cross section σ ... $\lambda = \frac{1}{n_s \sigma}$

In a material of width d with neutron MFP λ , probability for one neutron interaction is... $P = \int_0^d \frac{1}{\lambda} e^{-\frac{x}{\lambda}} dx$

Post-Scattering Energy Distribution of Fast Neutrons

Consider fast neutron with initial energy $E \gg k_B T$ scattering from a nucleus with mass number A at angle θ

Assume isotropic scattering $\frac{d\sigma}{d\Omega} = \frac{\sigma_{\text{tot}}}{4\pi}$

$$\alpha \equiv \frac{(A-1)^2}{(A+1)^2}$$

$$\frac{E'}{E} = \frac{A^2 + 2A \cos \theta + 1}{(A+1)^2}$$

$$E'_{\text{max}} = E, \quad E'_{\text{min}} = \alpha E \quad (\text{bounds on } E')$$

$$\frac{dP}{dE'} = \begin{cases} 0 & E' < \alpha E \\ \frac{1}{(1-\alpha)E} & E' \in (\alpha E, E) \\ 0 & E' > E. \end{cases} \quad (\text{distribution of } E')$$

Slowing Neutrons to Thermal Energy

Goal: slow neutron from $E_0 \gg k_B T$ to $E_T \sim k_B T$

$$\xi \equiv \langle \ln \frac{E_0}{E'} \rangle \implies \ln \frac{E'}{E_0} = -\xi \implies E' = E_0 e^{-\xi}$$

$$\xi = 1 + \frac{\alpha}{1-\alpha} \ln \alpha = 1 + \frac{(A-1)^2}{2A} \ln \frac{A-1}{A+1}$$

$$\xi \approx \frac{2}{A+2/3} \quad (\text{for heavy nuclei, } A \gtrsim 10)$$

$$\bar{\xi} \equiv \frac{\sum_i \sigma_i \xi_i}{\sum_i \sigma_i} \quad (\text{polyatomic materials})$$

$$E'_N = e^{-N\bar{\xi}} E_0 \quad (\text{energy after } N\text{-th collision})$$

$$N = \frac{1}{\bar{\xi}} \ln \frac{E_0}{E_T} \quad (\text{collisions to reach energy } E_T)$$

Cherenkov Radiation

Consider particle with charge $z = q/e_0$ moving along x axis in material with refractive index n at speed $v > c/n$

$$\cos \theta_C = \frac{1}{n\beta} \implies \theta_C = \cos^{-1} \frac{1}{n\beta} \quad (\text{Cherenkov angle})$$

$$\beta > 1/n \quad \text{or} \quad pc > \frac{mc^2}{\sqrt{1-(1/n^2)}} \quad (\text{thresholds for radiation})$$

$$\frac{d^2 E}{dx d\omega} = z^2 \frac{\alpha \hbar \omega}{c} \sin^2 \theta_C$$

$$\frac{d^2 N}{dx d\omega} = \frac{z^2 \alpha}{c} \sin^2 \theta_C = \frac{z^2 \alpha}{c} \left(1 - \frac{1}{(n\beta)^2}\right)$$

$$\frac{d^2 N}{dx d\lambda} = \frac{2\pi z^2 \alpha}{\lambda^2} \sin^2 \theta_C = \frac{2\pi z^2 \alpha}{\lambda^2} \left(1 - \frac{1}{(n\beta)^2}\right)$$

Cherenkov Detectors

Consider a detector sensitive to radiation in the range $\lambda_{\text{min}}, \lambda_{\text{max}}$ with efficiency $\eta(\lambda)$

$$N_{\text{det}} = d \int_{\lambda_{\text{min}}}^{\lambda_{\text{max}}} \eta(\lambda) \frac{d^2 N}{dx d\lambda} d\lambda$$

$$N_C \propto \sin^2 \theta_C = \left(1 - \frac{1}{(\beta n)^2}\right) \implies N_C \rightarrow N_{\text{max}} \text{ as } \beta \rightarrow 1$$

$$\langle N \rangle = \frac{N_{\text{max}}}{1-1/n^2} \left(1 - \frac{1}{\beta^2 n^2}\right) \equiv a \left(1 - \frac{1}{\beta^2 n^2}\right)$$

$$\implies \beta = \frac{1}{n \sqrt{1-(\langle N \rangle/a)}}$$